

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	92	(Lieber, Charles).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/02 09:31
S2	34	(Wu, Yue).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/02 09:31
S3	3	(Xiang, Jie).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/02 09:31
S4	169	(Yang, Chen).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/02 09:32
S5	194	(Lu, Wei).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/02 09:32
S6	1	PONTIS and STONAS and CHOW and PARCE	DERWENT	ADJ	ON	2009/06/02 10:04
S7	1	("20040136866").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/02 10:05
S8	1	("20030186522").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/02 10:12
S9	4	US-7254151-\$.DID. OR US- 7256466-\$.DID. OR US- 7301199-\$.DID. OR US- 20060160246-\$.DID.	US-PGPUB; USPAT; EPO; JPO	ADJ	ON	2009/06/02 10:17
S10	5	US-5866434-\$.DID. OR US- 6004444-\$.DID. OR US- 7385267-\$.DID. OR US- 20040075464-\$.DID. OR US- 20060057360-\$.DID.	US-PGPUB; USPAT; EPO; JPO	ADJ	ON	2009/06/02 10:34

S11	38	US-3873359-\$.DID. OR US-3873360-\$.DID. OR US-3900614-\$.DID. OR US-4673474-\$.DID. OR US-4939556-\$.DID. OR US-5023139-\$.DID. OR US-5089545-\$.DID. OR US-5252835-\$.DID. OR US-5274602-\$.DID. OR US-5453970-\$.DID. OR US-5475341-\$.DID. OR US-5512131-\$.DID. OR US-5524092-\$.DID. OR US-5537075-\$.DID. OR US-5539214-\$.DID. OR US-5581091-\$.DID. OR US-5589692-\$.DID. OR US-5607876-\$.DID. OR US-5620850-\$.DID. OR US-5640343-\$.DID. OR US-5726524-\$.DID. OR US-5739057-\$.DID. OR US-5747180-\$.DID. OR US-5751156-\$.DID. OR US-5776748-\$.DID. OR US-5824470-\$.DID. OR US-5830538-\$.DID. OR US-5840435-\$.DID. OR US-5847565-\$.DID. OR US-5858862-\$.DID. OR US-5864823-\$.DID. OR US-5897945-\$.DID. OR US-5900160-\$.DID. OR US-5903010-\$.DID. OR US-5908692-\$.DID. OR US-5916642-\$.DID. OR US-5942443-\$.DID. OR US-5997832-\$.DID.	US-PGPUB; USPAT; EPO; JPO	ADJ	ON	2009/06/02 10:47
S12	40	US-6036774-\$.DID. OR US-6038060-\$.DID. OR US-6060121-\$.DID. OR US-6060724-\$.DID. OR US-6069380-\$.DID. OR US-6123819-\$.DID. OR US-6128214-\$.DID. OR US-6143184-\$.DID. OR US-6149819-\$.DID. OR US-6159742-\$.DID. OR US-6180239-\$.DID. OR US-6187165-\$.DID. OR US-6190634-\$.DID. OR US-6203864-\$.DID. OR US-6207392-\$.DID. OR US-6211464-\$.DID. OR US-6231744-\$.DID. OR US-6256767-\$.DID. OR US-6270074-\$.DID. OR US-	US-PGPUB; USPAT; EPO; JPO	ADJ	ON	2009/06/02 10:52

		6278231-\$.DID. OR US- 6286226-\$.DID. OR US- 6287765-\$.DID. OR US- 6314019-\$.DID. OR US- 6325904-\$.DID. OR US- 6340822-\$.DID. OR US- 6346189-\$.DID. OR US- 6355198-\$.DID. OR US- 6359288-\$.DID. OR US- 6437329-\$.DID. OR US- 6459095-\$.DID. OR US- 6465132-\$.DID. OR US- 6468657-\$.DID. OR US- 6468677-\$.DID. OR US- 6503375-\$.DID. OR US- 6528020-\$.DID. OR US- 6538367-\$.DID. OR US- 6559468-\$.DID. OR US- 6586095-\$.DID. OR US- 6628053-\$.DID. OR US- 6716409-\$.DID.				
S13	40	US-6741019-\$.DID. OR US- 6743408-\$.DID. OR US- 6756025-\$.DID. OR US- 6756795-\$.DID. OR US- 6762056-\$.DID. OR US- 6781166-\$.DID. OR US- 6803840-\$.DID. OR US- 6808746-\$.DID. OR US- 6815706-\$.DID. OR US- 6846565-\$.DID. OR US- 6872645-\$.DID. OR US- 6882051-\$.DID. OR US- 6882767-\$.DID. OR US- 6902720-\$.DID. OR US- 6946197-\$.DID. OR US- 6958216-\$.DID. OR US- 6962823-\$.DID. OR US- 6974706-\$.DID. OR US- 6996147-\$.DID. OR US- 7048903-\$.DID. OR US- 7129554-\$.DID. OR US- 7172953-\$.DID. OR US- 7211464-\$.DID. OR US- 20010054709-\$.DID. OR US- 20020013031-\$.DID. OR US- 20020040805-\$.DID. OR US- 20020055239-\$.DID. OR US- 20020084502-\$.DID. OR US- 20020086335-\$.DID. OR US- 20020112814-\$.DID. OR US- 20020117659-\$.DID. OR US- 20020122766-\$.DID. OR US- 20020130311-\$.DID. OR US- 20020130353-\$.DID. OR US- 20020146714-\$.DID. OR US- 20020158342-\$.DID. OR US-	US-PGPUB; USPAT; EPO; JPO	ADJ	ON	2009/06/02 10:53

		20020172820-\$.DID. OR US- 20020175408-\$.DID. OR US- 20020179434-\$.DID. OR US- 20020187504-\$.DID.				
S14	40	US-20030001091-\$.DID. OR US-20030003300-\$.DID. OR US-20030032892-\$.DID. OR US-20030048619-\$.DID. OR US-20030073071-\$.DID. OR US-20030089899-\$.DID. OR US-20030098488-\$.DID. OR US-20030113713-\$.DID. OR US-20030113940-\$.DID. OR US-20030121764-\$.DID. OR US-20030124509-\$.DID. OR US-20030124717-\$.DID. OR US-20030134267-\$.DID. OR US-20030134433-\$.DID. OR US-20030135971-\$.DID. OR US-20030156992-\$.DID. OR US-20030186522-\$.DID. OR US-20030186544-\$.DID. OR US-20030189202-\$.DID. OR US-20030197456-\$.DID. OR US-20030200521-\$.DID. OR US-20040005723-\$.DID. OR US-20040026684-\$.DID. OR US-20040067530-\$.DID. OR US-20040095658-\$.DID. OR US-20040106203-\$.DID. OR US-20040112964-\$.DID. OR US-20040113138-\$.DID. OR US-20040113139-\$.DID. OR US-20040118448-\$.DID. OR US-20040136866-\$.DID. OR US-20040146560-\$.DID. OR US-20040157414-\$.DID. OR US-20040188721-\$.DID. OR US-20040213307-\$.DID. OR US-20050037374-\$.DID. OR US-20050064185-\$.DID. OR US-20050064731-\$.DID. OR US-20050066883-\$.DID. OR US-20050072213-\$.DID.	US-PGPUB; USPAT; EPO; JPO	ADJ	ON	2009/06/02 10:53
S15	27	US-20050079533-\$.DID. OR US-20050079659-\$.DID. OR US-20050100960-\$.DID. OR US-20050101026-\$.DID. OR US-20050109989-\$.DID. OR US-20050110064-\$.DID. OR US-20050161662-\$.DID. OR US-20050181587-\$.DID. OR US-20050201149-\$.DID. OR US-20050202615-\$.DID. OR US-20050212079-\$.DID. OR US-20050214967-\$.DID. OR US-20050219788-\$.DID. OR	US-PGPUB; USPAT; EPO; JPO	ADJ	ON	2009/06/02 10:54

		US-20050230356-\$.DID. OR US-20050253137-\$.DID. OR US-20050287717-\$.DID. OR US-20060008942-\$.DID. OR US-20060009003-\$.DID. OR US-20060019472-\$.DID. OR US-20060054936-\$.DID. OR US-20060175601-\$.DID. OR US-20060237749-\$.DID. OR US-20070026645-\$.DID. OR US-20070032023-\$.DID. OR US-20070032051-\$.DID. OR US-20070032052-\$.DID. OR US-20070048492-\$.DID.				
S16	1089	(silicide or salicide or suicide) and (nanowire or nanorod or nanostructure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/02 12:11
S17	3	(silicide or salicide or suicide or silicided) and (nanowire or nanorod or nanostructure) NOT S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/02 12:33
S18	871	(silicide or salicide or suicide) and (nanowire or nanorod or nanostructure) NOT ((silicide or salicide or suicide) with (catalyst or electrode))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/02 12:48
S19	101	(silicide or salicide or suicide) with (nanowire or nanorod or nanostructure) NOT ((silicide or salicide or suicide) with (catalyst or electrode))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/02 12:48
S20	17	("20020027819" "20020175390" "20030089899" "20030200521" "20030206436" "20040113138" "20040113139" "20050001918" "5349558" "6128214" "6211510" "6256767" "6314019" "6383784" "6777982" "7073157").PN. OR ("7310004").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/06/02 13:07

S21	20	(NiSi) with (nanowire or nanorod or nanostructure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/02 13:26
S22	12	(NiSi or nickel silicide or nickel monosilicide) with (nanowire or nanorod or nanostructure or nanoscale) NOT S21	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/02 14:00
S23	0	NSNW	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 07:37
S24	654	metallic (nanowire or nanorod or nanostructure or nanoscale)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 07:45
S25	14	silicidation with (nanowire or nanorod or nanostructure or nanoscale)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 08:04
S26	0	suicidation with (nanowire or nanorod or nanostructure or nanoscale)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 08:23
S27	0	salicidation with (nanowire or nanorod or nanostructure or nanoscale)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 08:23
S28	7	salicide with (nanowire or nanorod or nanostructure or nanoscale)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 08:24
S29	4	("20030124845" "4814294" "5780632" "6962873").PN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2009/06/03 08:28

S30	157	silicide with (nanowire or nanorod or nanostructure or nanoscale)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 08:29
S31	10	suicide with (nanowire or nanorod or nanostructure or nanoscale)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 08:30
S32	734	mask with (nanowire or nanorod or nanostructure or nanoscale)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 08:50
S33	1	("20050017234").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 09:30
S34	11	nanoscale MOSFET	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 10:19
S35	6	nanoscale MOS	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 10:53
S36	7264	silicide with mask	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 11:01
S37	6	silicide with mask with nanowire	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 11:05
S38	146	mask with (nanowire or nanorod or nanostructure or nanoscale) and (silicide or salicide or suicide or salicidation or silicidation or suicidation)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 11:06

S39	1167	silicide with mask with photoresist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 11:18
S40	363	silicide with mask with photoresist with pattern	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 11:18
S41	248	silicide with mask with photoresist with pattern and (@AD< "20040212")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 11:19
S42	10	mask adj5 protect\$3 adj5 silicidation and (@AD< "20040212")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 11:37
S43	32	mask adj5 prevent\$3 adj5 silicidation and (@AD< "20040212")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/03 11:44
S44	992	(257/14).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 12:08
S46	856	(257/E21.199).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 12:09
S47	927	(438/660).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 12:09
S48	623	(438/664).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 12:09
S49	199	(977/700).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 12:09
S50	281	(977/762).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 12:09
S51	68	(977/810).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 12:09
S52	53	(977/813).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 12:10
S53	24	(977/814).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 12:10
S54	204	(977/890).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 12:10

S55	245	(977/900).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 12:10
S56	1	("6897098").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/06/03 12:51
S57	734	(mask) with (nanowire or nanorod or nanostructure or nanoscale)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/04 10:02
S58	19	(mask) with (nanowire or nanorod or nanostructure or nanoscale) with (core or shell)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/04 10:12
S59	12	US-6451113-\$.DID. OR US-6440637-\$.DID. OR US-7335908-\$.DID. OR US-7399691-\$.DID. OR US-20040191517-\$.DID. OR US-20050266662-\$.DID. OR US-20050117441-\$.DID. OR US-20060269927-\$.DID. OR US-20070281156-\$.DID. OR US-20070252136-\$.DID. OR US-20080191196-\$.DID. OR US-20090004852-\$.DID.	US-PGPUB; USPAT; EPO; JPO	ADJ	ON	2009/06/09 13:01
S60	14	US-20080254291-\$.DID. OR US-20080211040-\$.DID. OR US-20080161876-\$.DID. OR US-20090057650-\$.DID. OR US-5882779-\$.DID. OR US-5985173-\$.DID. OR US-6248674-\$.DID. OR US-6900479-\$.DID. OR US-6963077-\$.DID. OR US-7073157-\$.DID. OR US-7274208-\$.DID. OR US-7476596-\$.DID. OR US-7500213-\$.DID. OR US-7595260-\$.DID.	US-PGPUB; USPAT; USOCR; JPO	ADJ	ON	2010/01/13 20:17
S61	24	("20030006410" "20040136866" "5612255" "5858256" "6103540").PN. OR ("6897098").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/01/13 20:29
S62	12	(silicon near3 nanowires with silicide) and (@ad< "20040615")	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/01/13 20:35
S63	14	(nanowires with silicide) and (@ad< "20040615") NOT S62	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/01/13 20:41

S64	1027	("500" nm with gate) and (@ad<"20040614")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/13 20:59
S65	36	("500" nm with gate with silicide) and (@ad<"20040614")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/13 20:59
S66	55	(width with nm with gate) and (anneal with silicide) and (@ad<"20040614")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/13 21:06
S67	21	(width with gate) and (anneal with silicide with nickel) and (@ad<"20040614")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/13 21:28
S68	3	("5840618" "6331468").PN. OR ("6486062").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/01/13 21:44
S69	0	selectively siliciding gate lines	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/01/13 21:46
S70	0	selectively with siliciding wiht gate lines	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/01/13 21:46
S71	0	selectively with siliciding with gate lines	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/01/13 21:46
S72	7	selectively with mask with siliciding with (gate or lines) and (@ad<"20040614")	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/01/13 21:47
S73	28	(silicide and salicide or suicide) and FINFET and (nanometers or nm or microns) and (@ad<"20030614")	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/01/13 21:49
S74	15	(silicide and salicide or suicide) and FINFET and ((nanometers or nm or microns) with (width or length)) and (@ad<"20030614")	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/01/13 21:50
S75	2	"20040036127"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 09:09

S76	6	"7358121"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 09:10
S77	1	("7358121").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/14 09:11
S78	1	("6740565").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/14 09:43
S79	2451	silicide with photoresist	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 09:51
S80	1648	silicide with photoresist and (@AD<"20030614")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 09:52
S81	0	silicide with photoresist and FINFET and (@AD<"20030614")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 09:52
S82	80	silicide with photoresist and ((width or length) with nm) and (@AD<"20030614")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 09:52
S91	433	(silicide with photoresist) NOT (silicide with photoresist with (etch or etched or etching or remove or removed or removing or removal or stripped or stripping or reflected or reflection or reflective or ARC or ARL)) and (@AD<"20030614")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 10:13
S92	5	(silicide with photoresist) same anneal NOT (silicide with photoresist with (etch or etched or etching or remove or removed or removing or removal or stripped or stripping or reflected or reflection or reflective or ARC or ARL)) and (@AD<"20030614")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 10:15

S94	51	((silicide or salicide or suicide) with photoresist) same (anneal or annealed or annealing or heat or heated or heating) NOT ((silicide or salicide or suicide) with photoresist with (etch or etched or etching or remove or removed or removing or removal or stripped or stripping or reflected or reflection or reflective or ARC or ARL)) and (@AD<"20030614")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 10:16
S95	1	("5744839").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/14 11:27
S96	561	(438/674).OCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/14 12:50
S97	969	(438/682).OCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/14 12:50
S98	15	S96 and S97 and (@AD<"20040615")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 12:51
S99	244	(S96 or S97) and silicide and photoresist and (@AD<"20040615")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 12:52
S100	721	(S96 or S97) and (@AD<"20040615") NOT S99	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 13:52
S101	545	(S96 or S97) NOT S99 NOT S100	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/01/14 13:52
S102	686	(257/E29.156).OCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/14 14:00
S103	219	(257/E21.148).OCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/14 14:00
S104	2141	(257/E21.165).OCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/14 14:00
S105	795	(257/E21.295).OCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/14 14:01

S106	234	(257/E21.296).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/01/14 14:01
S107	3	"7619290"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/22 10:56
S108	1	("7629629").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/05/24 09:32
S109	3	US-7067867-\$.DID. OR US- 20050212079-\$.DID. OR US- 20060008942-\$.DID.	US-PGPUB; USPAT; USOCR; JPO	ADJ	ON	2010/05/24 09:36
S110	87	(Saitoh, Tohru).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 09:41
S111	37	(Wu, Yue).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 10:00
S113	30	si nanowire with transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 12:37
S114	2	si nanowire with transistor and (@AD<"20040212")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 12:39
S115	29	silicon nanowire with transistor and (@AD<"20040212")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 12:39
S116	8	("20030006410" "20050006671" "20050037547" "5646058" "6597090" "6784028" "6858478" "6897098").PN. OR ("7101761").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/05/24 12:50

S117	3	silicon (nanowire or nanorod or nanostructure) with (free standing or solution) same transistor and (@AD<"20040212")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 13:16
S118	2	si (nanowire or nanorod or nanostructure) with transistor and (@AD<"20040212")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 13:24
S119	41	silicon (nanowire or nanorod or nanostructure) same transistor and (@AD<"20040212")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 13:27
S121	11	silicon (nanowire or nanorod or nanostructure) same silicide and (@AD<"20040212")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 13:33
S122	11	silicon (nanowire or nanorod or nanostructure) same (silicide or salicide or suicide or (react with metal)) and (@AD<"20040212")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 13:39
S123	42	silicon (nanowire or nanorod or nanostructure) and (silicide or salicide or suicide or (react with metal)) and (@AD<"20030612")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 13:45
S125	39	silicon with (nanowire or nanorod or nanostructure) and (silicide or salicide or suicide or (react with metal)) and (@AD<"20030612") NOT S123	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 13:50
S132	0	((nanowire or nanorod or nanostructure) with channel) and (nickel with contact) and (@AD<"20030612")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 15:10
S133	108	((nanowire or nanorod or nanostructure) with channel) and (@AD<"20030612")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 15:10

S135	35	((nanowire or nanorod or nanostructure) with channel) and (metal with (source or drain or contact)) and (@AD<"20030612")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 15:11
S136	67	(Weber).in. and (nanowire or nanostructure or nanorod)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 15:24
S137	6	(Weber).in. and (nanowire or nanostructure or nanorod) and silicide	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 15:24
S138	3	(Weber, Walter).in. and (nanowire or nanostructure or nanorod)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 15:30
S139	376	(Weber, Walter).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/05/24 15:30

EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S127	16	(method and metal and silicide and (nanowire or nanostructure or nanorod)).CLM.	USPAT; UPAD	ADJ	ON	2010/05/24 10:11
S129	141	(method with (metal or silicide) with (nanowire or nanostructure or nanorod)).CLM.	USPAT; UPAD	ADJ	ON	2010/05/24 10:13
S130	5	(method with (silicide) with (nanowire or nanostructure or nanorod)).CLM.	USPAT; UPAD	ADJ	ON	2010/05/24 10:20
S131	49	(method with (conductive) with (nanowire or nanostructure or nanorod)).CLM.	USPAT; UPAD	ADJ	ON	2010/05/24 10:24

5/ 25/ 2010 11:14:16 AM

C:\ Documents and Settings\ dwolverton\ My Documents\ EAST\ Workspaces\ 10588833.wsp